

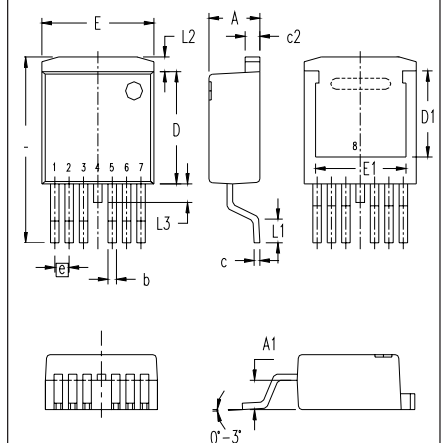
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
(T _J = 25°C unless otherwise specified)				
g_{fs}	V _{DS} = 10 V; I _D = 60 A, Note 1	70	110	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		6900	pF
C_{oss}			923	pF
C_{rss}			162	pF
t_{d(on)}	Resistive Switching Times		33	ns
t_r	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 25 A		54	ns
t_{d(off)}	R _G = 3.3 Ω (External)		42	ns
t_f			31	ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 25 A		151	nC
Q_{gs}			39	nC
Q_{gd}			45	nC
R_{thJC}				0.31 °C/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
T _J = 25° C unless otherwise specified)				
I _S	V _{GS} = 0 V			180 A
I _{SM}	Pulse width limited by T _{JM}			450 A
V _{SD}	I _F = 25 A, V _{GS} = 0 V, Note 1			0.95 V
t _{rr}	I _F = 25 A, -di/dt = 100 A/μs V _R = 50 V, V _{GS} = 0 V		100	ns

Notes: 1. Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %.

TO-263 (7-lead) (IXTA...7) Outline



Pins: 1 - Gate
2, 3 - Source
4 - Drain
5, 6, 7 - Source
Tab (8) - Drain

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.085	.104	2.15	2.65
b	.026	.035	0.65	0.90
c	.016	.024	0.40	0.60
c2	.049	.055	1.25	1.40
D	.355	.370	9.00	9.40
D1	.272	.280	6.90	7.10
E	.386	.402	9.80	10.20
E1	.311	.319	7.90	8.10
e	.050 BSC		1.27 BSC	
L	.591	.614	15.00	15.60
L1	.091	.110	2.30	2.80
L2	.039	.059	1.00	1.50
L3	.000	.059	0.00	1.50

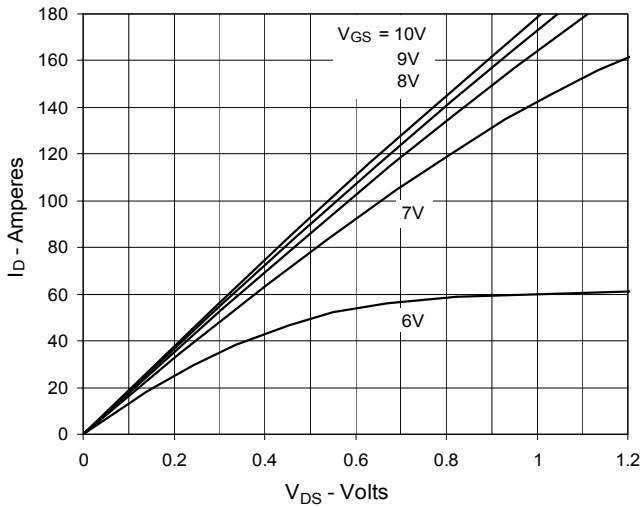
PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

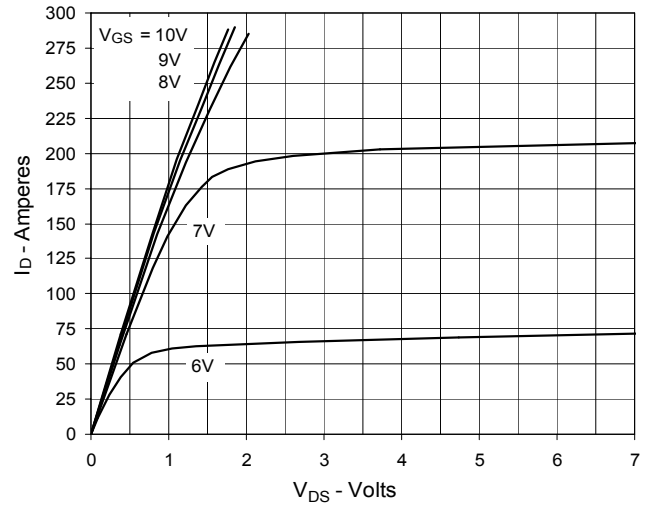
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537

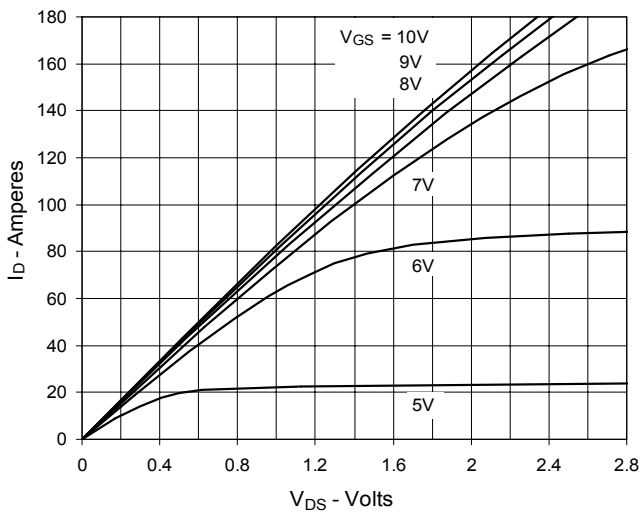
**Fig. 1. Output Characteristics
@ 25°C**



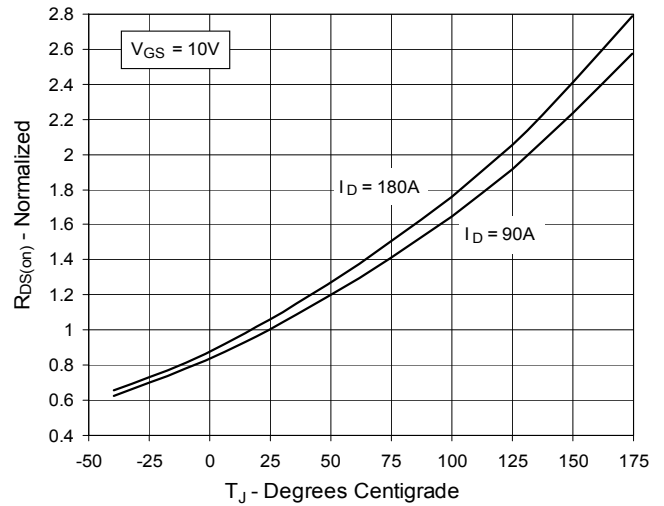
**Fig. 2. Extended Output Characteristics
@ 25°C**



**Fig. 3. Output Characteristics
@ 150°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 90A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 90A$ Value
vs. Drain Current**

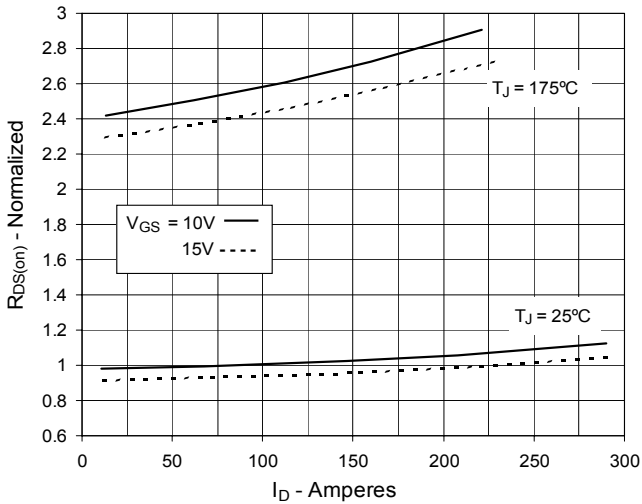


Fig. 6. Drain Current vs. Case Temperature

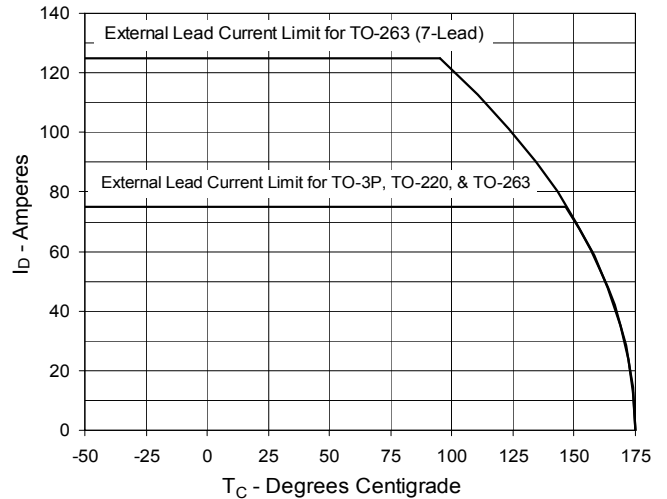
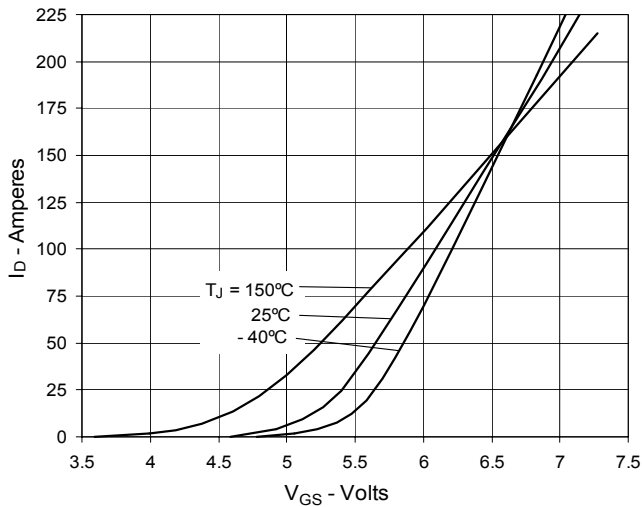
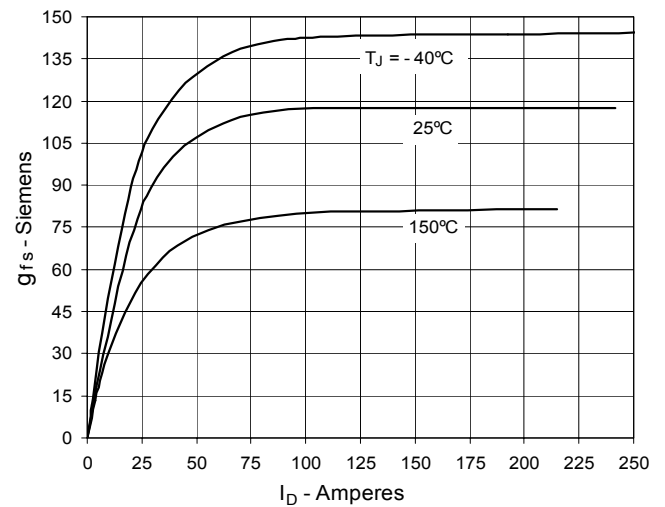
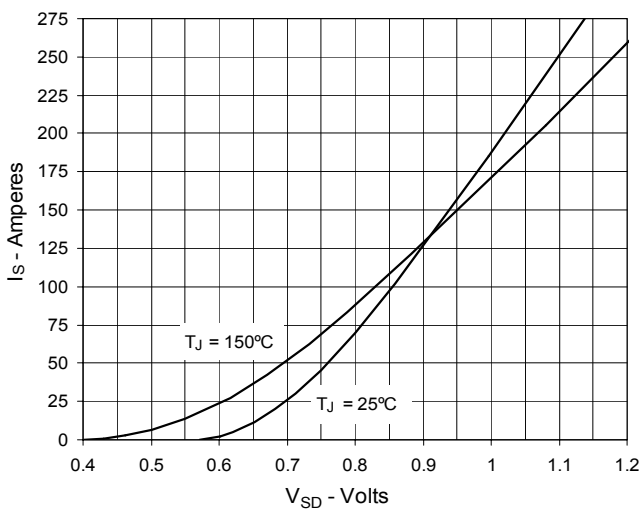
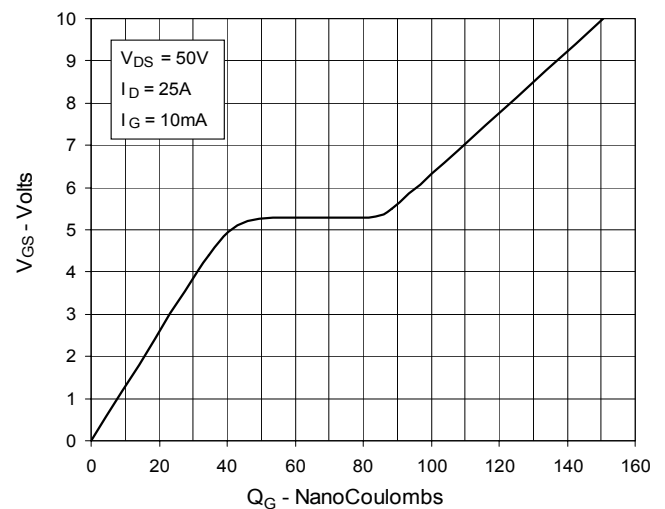
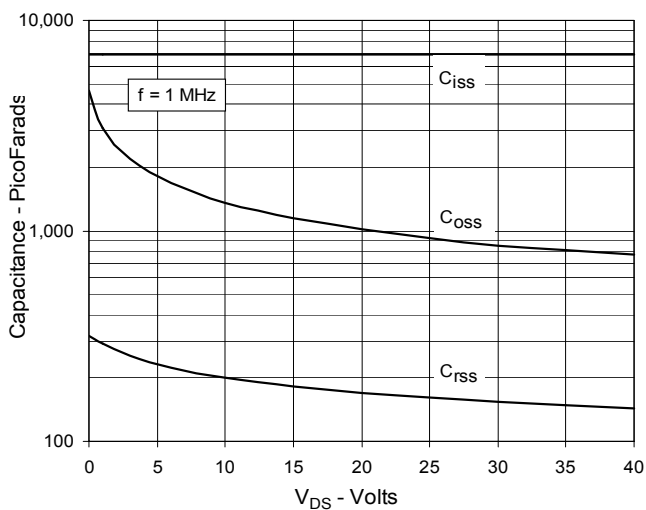
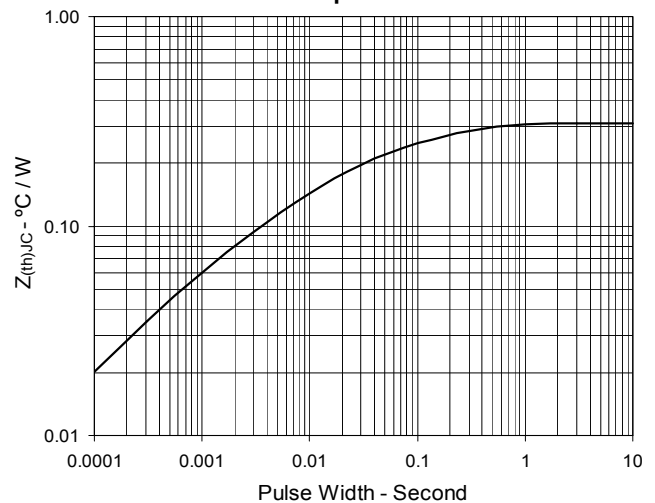
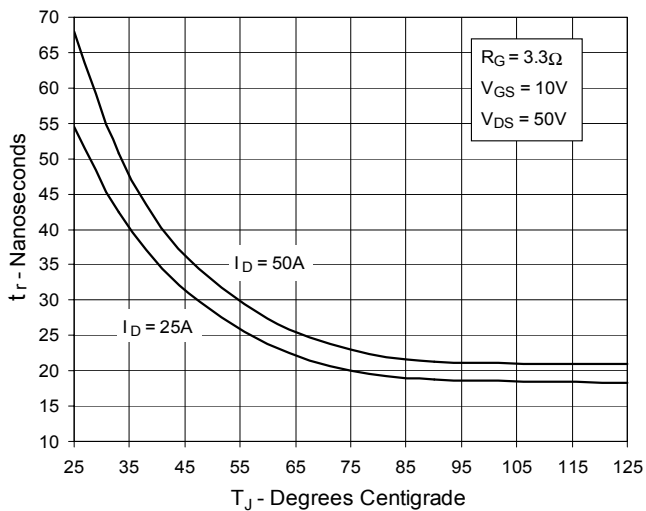
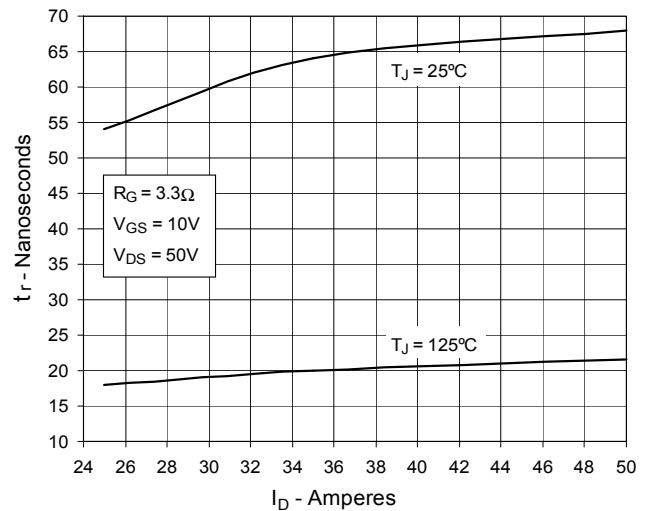


Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Maximum Transient Thermal Impedance


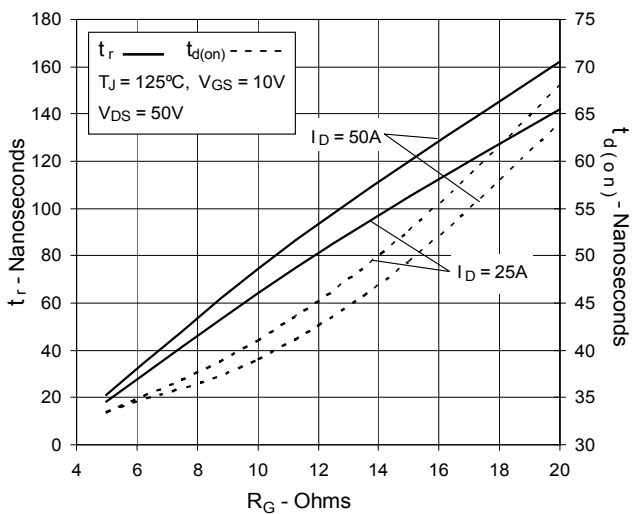
**Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature**



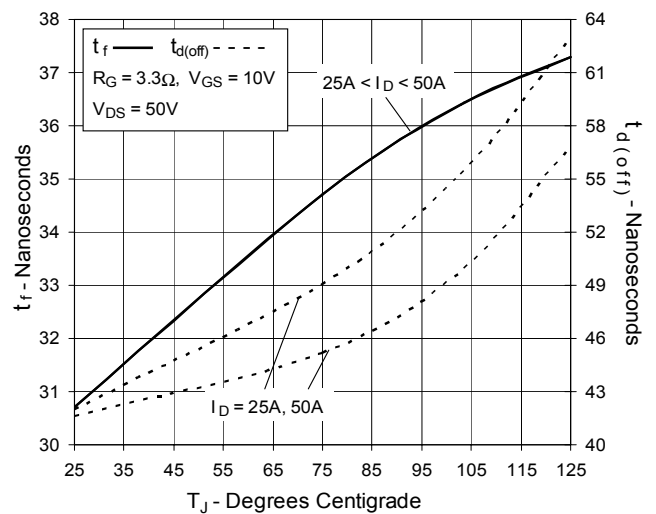
**Fig. 14. Resistive Turn-on
Rise Time vs. Drain Current**



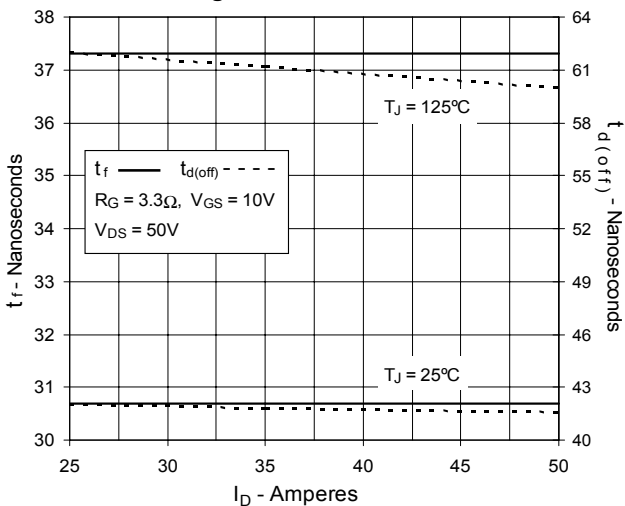
**Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance**



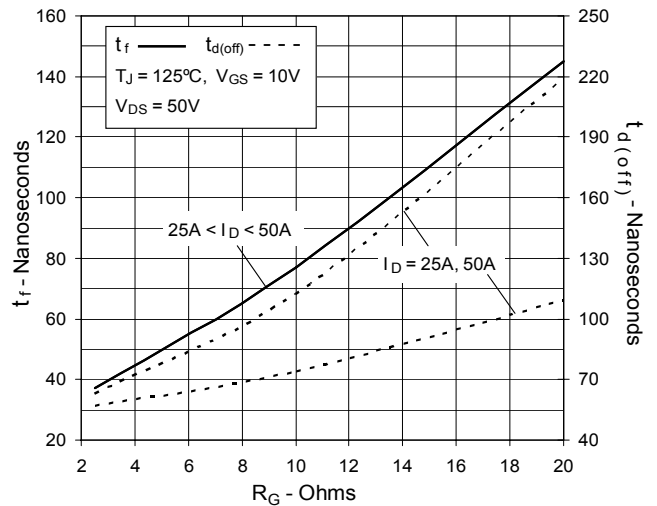
**Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off
Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance**





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